

**FEATURES**

- Square Active Area
- Ideal for 190-400 nm Detection
- 100% Internal QE
- Excellent UV Response
- Protective Cover Plate<sup>2</sup>

**Electro-Optical Characteristics at 25 °C**

Parameters	Test Conditions	Min	Typ	Max	Units
Active Area	10 mm x 10 mm		100		mm <sup>2</sup>
Responsivity	@ 254 nm	0.08	0.09		A/W
Shunt Resistance	@ ± 10 mV	20			MOhms
Reverse Breakdown Voltage, V <sub>R</sub>	I <sub>R</sub> = 1 µA	5	10		Volts
Capacitance, C	V <sub>R</sub> = 0 V		1	3	nF
Response Time	RL = 50 Ω, V <sub>R</sub> = 10 V			10	usec

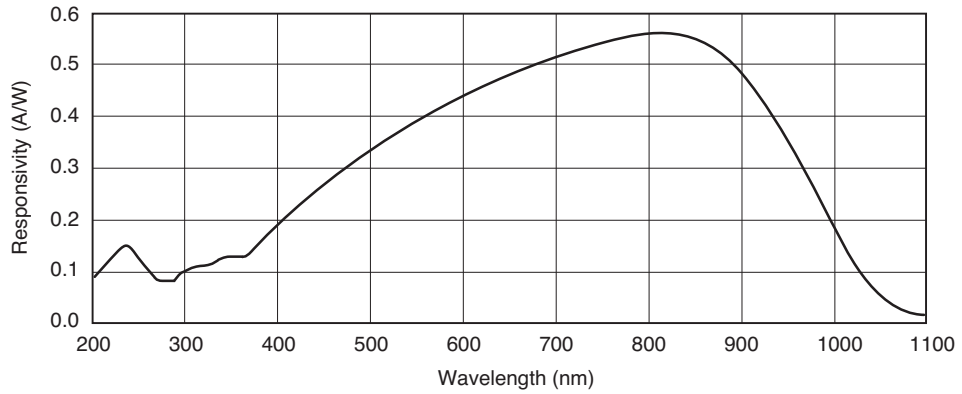
**Thermal Parameters**

Storage and Operating Temperature Range	Units
Storage Temperature Range	-20° to 100°C
Operating Temperature Range	-20° to 80°C
Maximum Junction Temperature	100 °C
Lead Soldering Temperature <sup>1</sup>	240°C

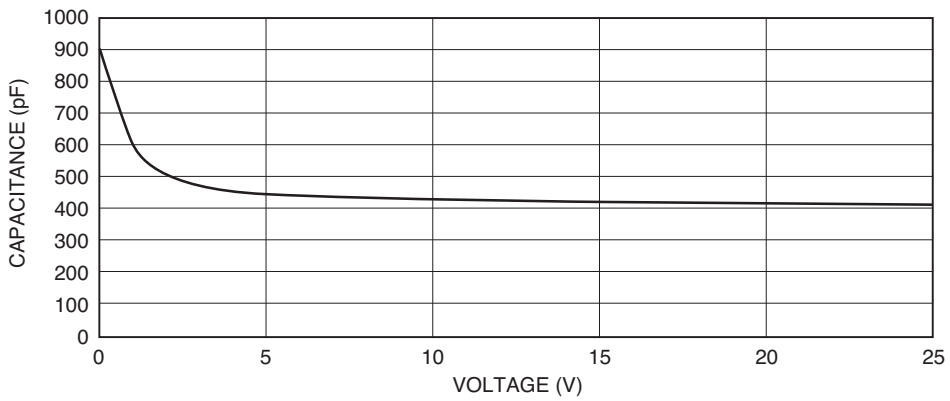
<sup>1</sup> 0.08" from case for 10 seconds.

<sup>2</sup> Shipped with temporary cover to protect the photodiode and wire bonds.  
 Review the Application Note, "Handling Precautions for AXUV, SXUV, and UVG Detectors", prior to removing cover.

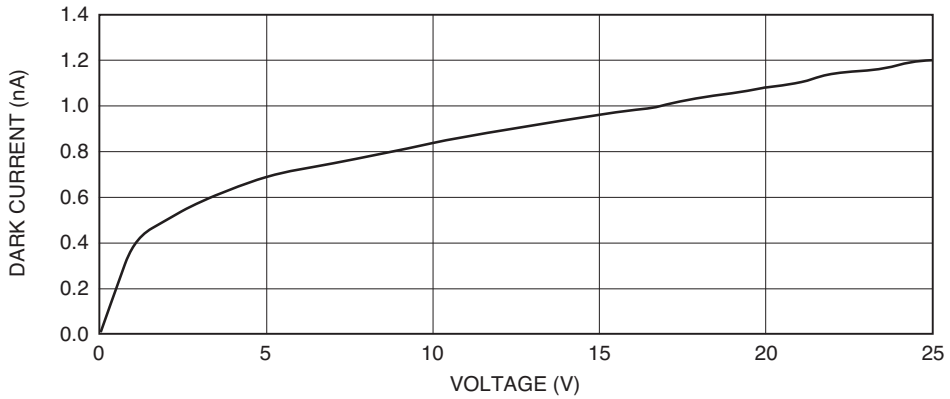
Typical Photon Responsivity



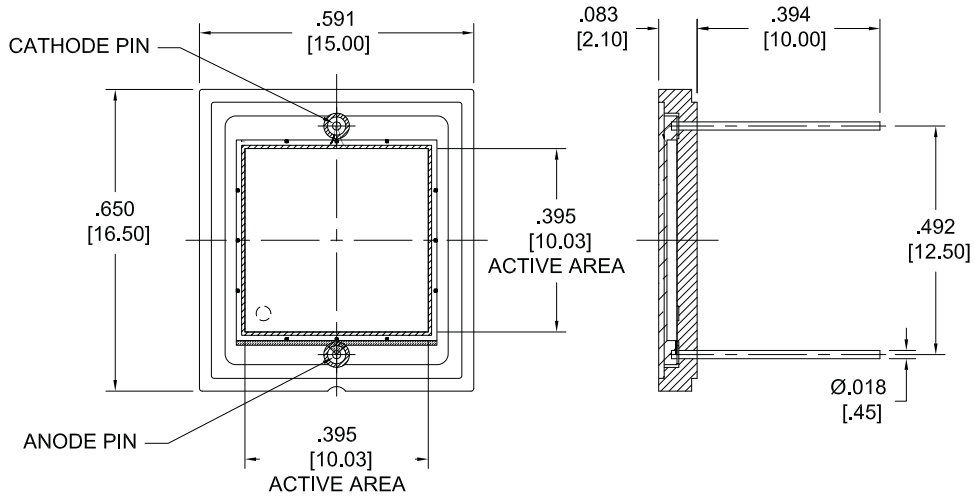
Capacitance vs. Voltage



Dark Current vs. Voltage



Package Information



Dimensions are in inch [metric] units.

Specifications are subject to change without prior notice.